



BSS84

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	Ι _D T _A = 25°C
-50V	10Ω @ V _{GS} = -5V	-130mA

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- **Power Management Functions**
- Analog Switch

Features and Benefits

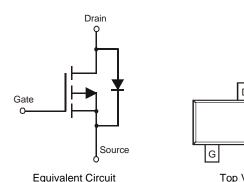
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed •
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

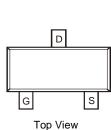
Mechanical Data

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View





Ordering Information (Note 3)

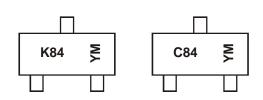
Part Number	Qualification	Case	Packaging
BSS84-7-F	Commercial	SOT23	3000/Tape & Reel
BSS84Q-7-F	Automotive	SOT23	3000/Tape & Reel
BSS84-13-F	Commercial	SOT23	10000/Tape & Reel
BSS84Q-13-F	Automotive	SOT23	10000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

2. Product manufactured with Date Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb_2O_3 Fire Retardants

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K = SAT (Shanghai Assembly / Test site) C = CAT (Chengdu Assembly / Test site)

- 84 = Product Type Marking Code
- YM = Date Code Marking
- Y = Year (ex: N = 2002)
- M = Month (ex: 9 = September)

Date Code Kev

Date Couciney															
Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	К	L	Μ	Ν	Р	R		Y	Z	А	В	С	D	E
Month	Jan	Fel	o I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \le 20K\Omega$		V _{DGR}	-50	V
Gate-Source Voltage	Continuous	V _{GSS}	±20	V
Drain Current (Note 4)	Continuous	I _D	-130	mA
Pulsed Drain Current		IDM	-1.2	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	PD	300	mW
Thermal Resistance, Junction to Ambient	R _{0JA}	417	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	۵°

Electrical Characteristics @T_A = 25°C unless otherwise specified

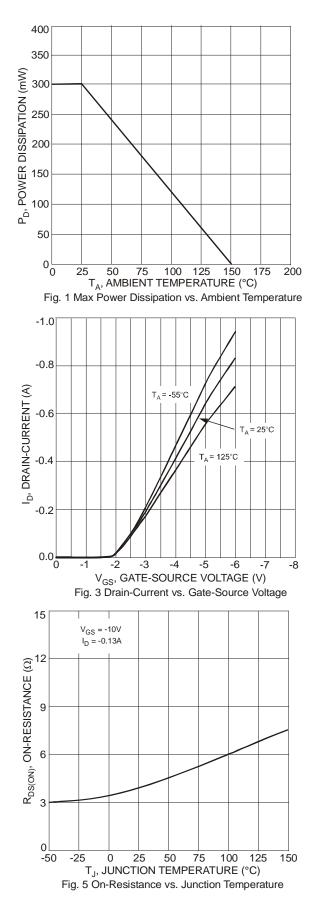
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	-50	_	_	V	V _{GS} = 0V, I _D = -250µA	
			_	-15	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C	
Zero Gate Voltage Drain Current	IDSS		—	-60	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C	
				-100	nA	$V_{DS} = -25V, V_{GS} = 0V, T_{J} = 25^{\circ}C$	
Gate-Body Leakage	IGSS			±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	-0.8		-2.0	V	$V_{DS} = V_{GS}, I_D = -1mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}		_	10	Ω	V _{GS} = -5V, I _D = -0.100A	
Forward Transconductance	g fs	0.05			S	V _{DS} = -25V, I _D = -0.1A	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss			45	pF		
Output Capacitance	Coss			25	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}			12	pF		
SWITCHING CHARACTERISTICS (Note 6)	· ·		•				
Turn-On Delay Time	t _{D(ON)}		10		ns	$V_{DD} = -30V, I_D = -0.27A,$	
Turn-Off Delay Time	t _{D(OFF)}		18		ns	R _{GEN} = 50Ω, V _{GS} = -10V	

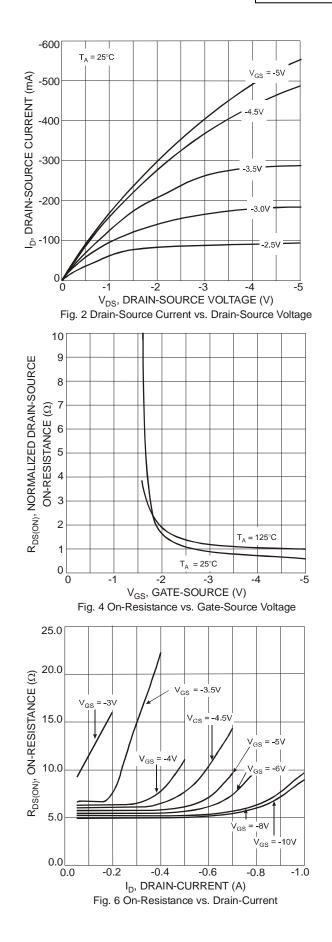
Notes: 4. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001,

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing



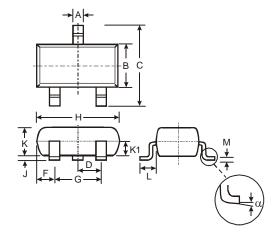






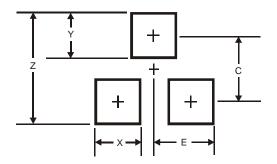


Package Outline Dimensions



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
κ	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All	Dimens	ions in	mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35



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